

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1379	(PZT or BST or TaO2 or "TaO.sub.2" or HfO2 or "HfO.sub.2" or ZrO2) same etch\$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:43
L2	247	(PZT or BST or TaO2 or "TaO.sub.2" or HfO2 or "HfO.sub.2" or ZrO2) same etch\$4 same plasma	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:14
L3	2320	(chlorine or "Cl.sub.2" or BCI3 or "BCI.sub.3" or HCl) same "carbon monoxide"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:18
L6	783	(chlorine or "Cl.sub.2" or BCI3 or "BCI.sub.3" or HCl) same "carbon monoxide" same (AR or argon or oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 08:00
L7	32698	(PZT or BST or TaO2 or "TaO.sub.2" or HfO2 or "HfO.sub.2" or ZrO2)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:20
L12	72	6 and dielectric	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:23
L14	390	(chlorine or "Cl.sub.2" or BCI3 or "BCI.sub.3" or HCl) with "carbon monoxide" with (AR or argon or oxygen or "O.sub.2")	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:33
L15	58	14 and semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:29
L16	627	(PZT or BST or TaO2 or "TaO.sub.2" or HfO2 or "HfO.sub.2" or ZrO2) with etch\$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:45
L18	108	(PZT or BST or TaO2 or "TaO.sub.2" or HfO2 or "HfO.sub.2" or ZrO2) with etch\$4 with plasma	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 07:46
L19	0	(chlorine or "Cl.sub.2" or BCI3 or "BCI.sub.3" or HCl) same "carbon monoxide" same (AR or argon or oxygen or "O.sub.2") same ferroelectric	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 08:01

L21	1	ferroelectric same etch\$4 same "carbon monoxide"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 08:09
L22	2102	ferroelectric same etch\$4	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/02/17 08:09